

1. A voltage reference in an integrated circuit, formed of an NPN bipolar transistor, a base of which is not connected and a emitter of which corresponds to an anode, and a collector of which corresponds to a cathode.
2. The voltage reference of claim 1, wherein the transistor is an NPN bipolar transistor of a bipolar-type integrated circuit.
3. The voltage reference of claim 1, wherein the NPN bipolar transistor is formed in an N well of a MOS-type integrated circuit, the emitter corresponding to a drain-source region of an N-channel MOS transistor formed in a region corresponding to a drain-source region of a P-channel MOS transistor.